## Analysis of Strain-induced Pockels effect in Silicon

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Introduction: The discovered Pockels effect in strained silicon has made silicon a promising candidate material for realizing optical modulators and switches [1].

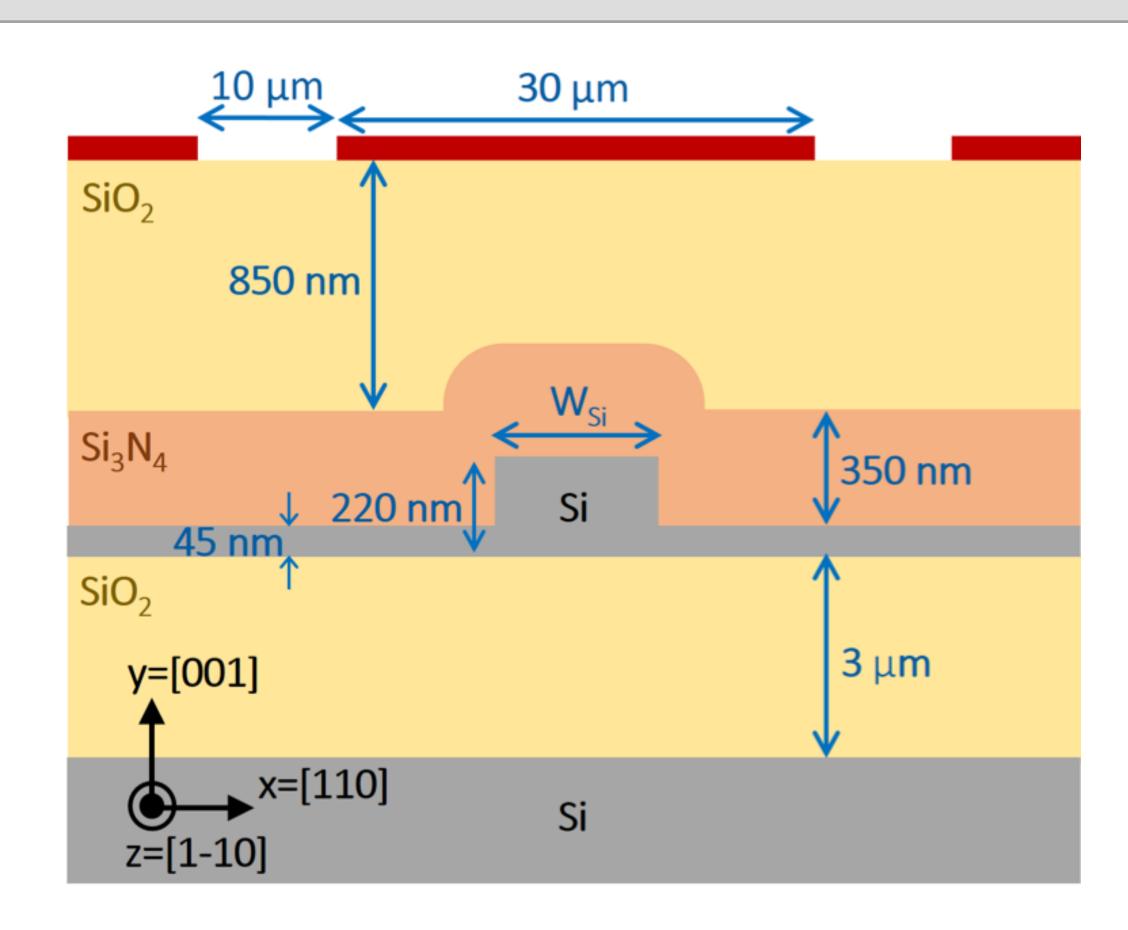


Fig. 1. MZI cross section designed for Pockels effect analysis [1].

Theory: We assume that  $\chi^{(2)}$  is local function of  $\epsilon$  and develop in Taylor series

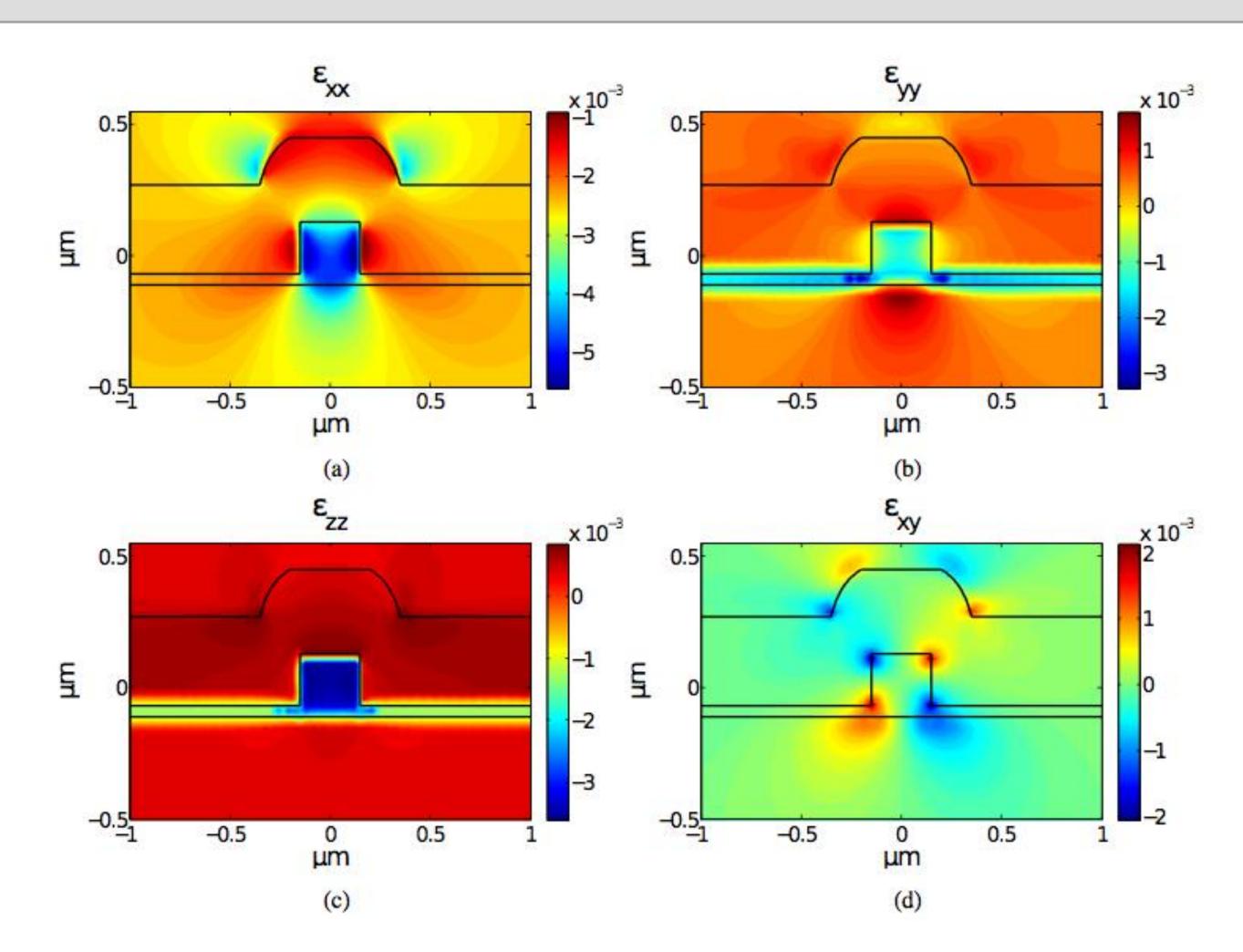
$$\chi_{ijk}^{(2)} = \frac{\partial \chi_{ijk}^{(2)}}{\partial \zeta_{\alpha\beta\gamma}} \bigg|_{\varepsilon=0} \zeta_{\alpha\beta\gamma}$$

where  $\zeta_{\alpha\beta\gamma} = \partial \varepsilon_{\alpha\beta}/\partial x_{\gamma}$  is the strain gradient tensor. The final expression for the effective dielectric susceptibility is given by

$$\chi_{v}^{eff}(\omega) = c_i o_i(\omega)$$

where  $o_i(\omega)$  are combination of the weighted strain gradients.

USE of COMSOL Multiphysics: The strain profiles are computed taking into account the orthotropic model in ref [3] and the waveguide show a single mode behaviour.



**Fig. 2**. Strain profiles for the cross section of ref [1] computed by taking into account ref. [3]

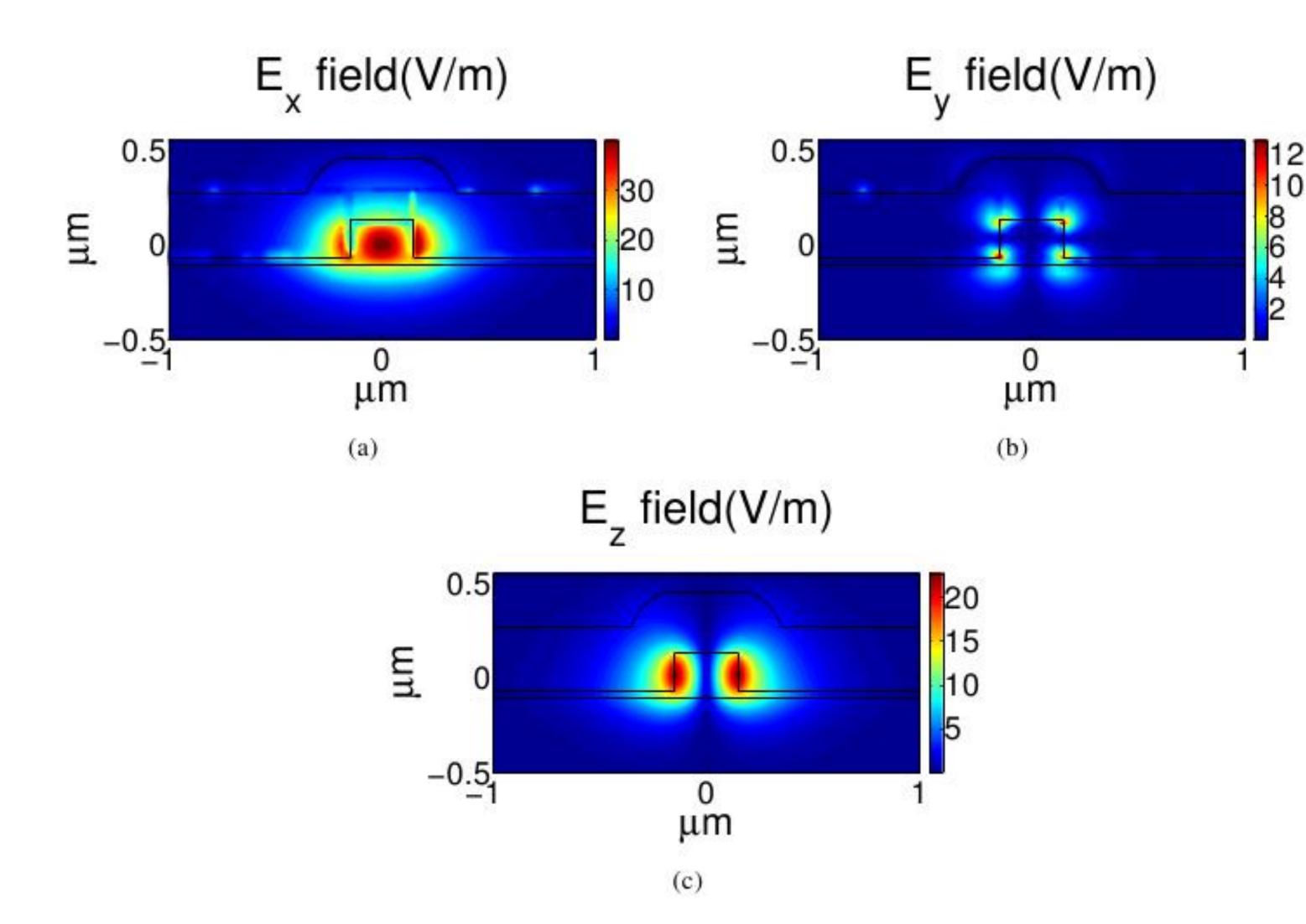
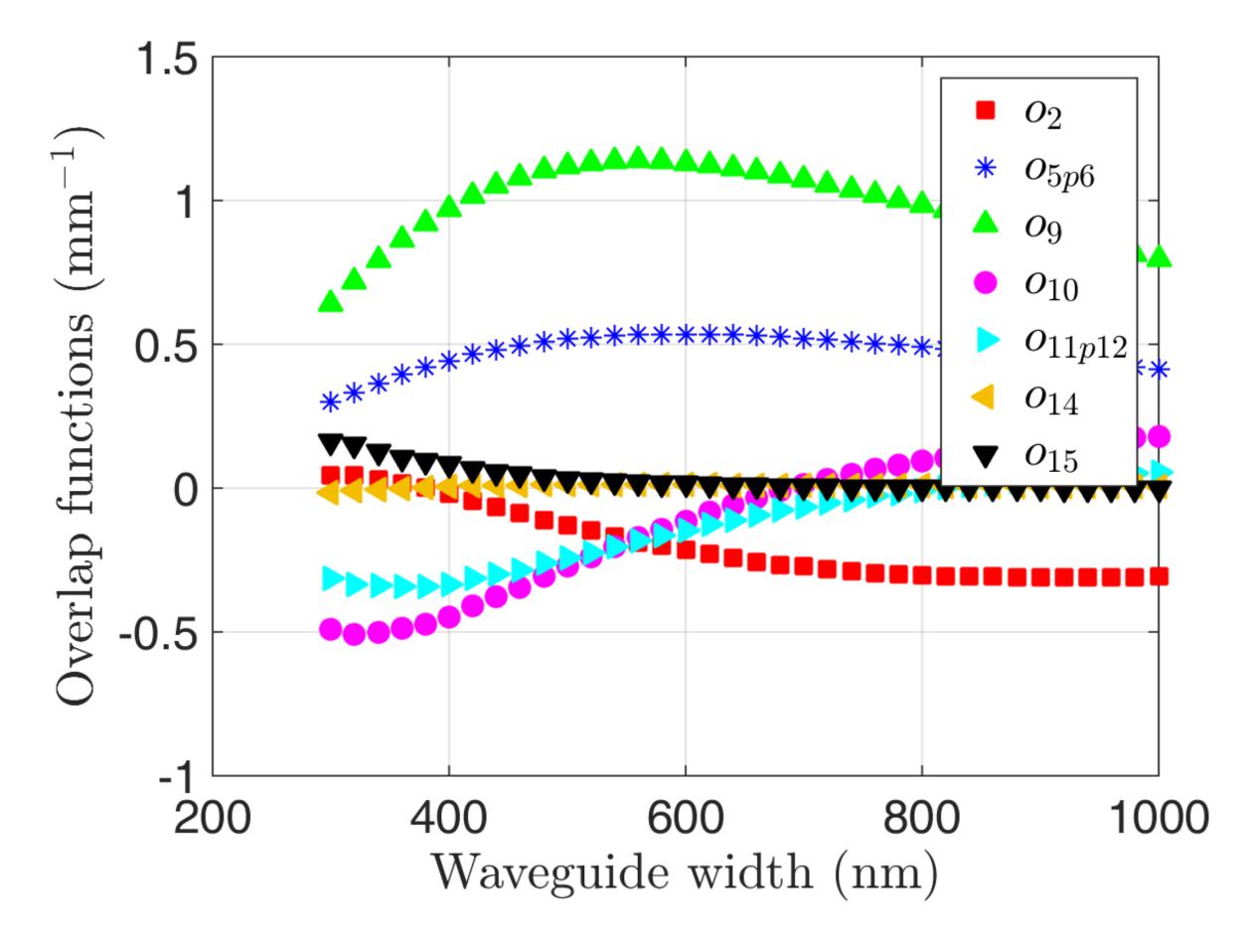


Fig. 3. The mode analysis for the waveguide cross section in ref. [1]

Results and conclusions: From the combination of the mode analysis and the mechanical deformation we obtained the values of the overlap integrals. Future experimental data will give the possibility of evaluating the  $c_i$  coefficients



**Fig. 4**. Overlap integrals for the waveguide cross section as function of the waveguide width ref. [1]

## References:

- 1. B. Chmielak, et al., "Investigation of local strain distribution and linear electro-optic effect in strained silicon waveguides," *Opt. Express*, **21**, (2013).
- 2. B. Chmielak et al., "Pockels effect based fully integrated, strained silicon electro-optic modulator," *Opt. Express*, **19**, (2011)
- 3. M. A. Hopcroft et al. "What is the Young's modulus of silicon?," *IEEE Journal of Microelectromechanical Systems*, **19**, (2010).